



RF power transistor, LdmoST family

Features

- Excellent thermal stability
- Common source configuration
- P_{OUT} = 35 W with 14.5 dB gain @ 945 MHz / 13.6 V
- BeO-free ceramic package
- ESD protection
- In compliance with the 2002/95/EC european directive

Description

The PD85035C is a common source N-channel, enhancement-mode lateral Field-Effect RF power transistor. It is designed for high gain, broadband commercial and industrial applications. It operates at 13.6 V in common source mode at frequencies of up to 1 GHz. PD85035C boasts the excellent gain, linearity and reliability of ST's latest LDMOS technology. PD85035C's superior linearity performance makes it an ideal solution for car mobile radio.

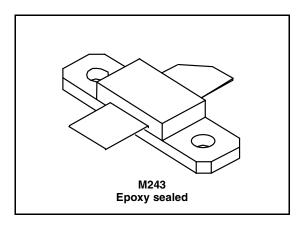


Figure 1. Pin connection

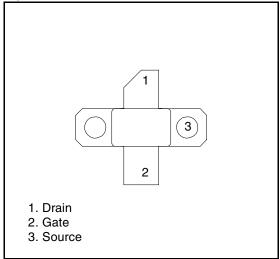


Table 1. Device summary

Part number	Package	Packaging
PD85035C	M243	Box

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PD85035C Electrical data

1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings $(T_{CASE} = 25 \, ^{\circ}C)$

Symbol	Parameter	Value	Unit	
V _{(BR)DSS}	Drain-source voltage	40	V	
V _{GS}	Gate-source voltage	-0.5 to +15	V	
I _D	Drain current	8	Α	
P _{DISS}	Power dissipation (@ T _C = 70 °C)	108	W	
TJ	Max. operating junction temperature	200	°C	
T _{STG}	Storage temperature -65 to +150			

1.2 Thermal data

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Junction - case thermal resistance	1.2	°C/W

Electrical characteristics PD85035C

2 Electrical characteristics

$$T_{CASE} = +25$$
 °C

2.1 Static

Table 4. Static

Symbol		Min	Тур	Max	Unit		
I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 25 V				1	μΑ
I _{GSS}	V _{GS} = 20 V	$V_{DS} = 0 V$				1	μΑ
$V_{GS(Q)}$	V _{DS} = 10 V	$I_D = 350 \text{ mA}$			3.9		٧
V _{DS(ON)}	V _{GS} = 10 V	I _D = 3 A			0.64	0.7	٧
C _{ISS}	$V_{GS} = 0 V$	$V_{DS} = 12.5 \text{ V}$	f = 1 MHz		76		pF
Coss	V _{GS} = 0 V	V _{DS} = 12.5 V	f = 1 MHz		45		pF
C _{RSS}	V _{GS} = 0 V	V _{DS} = 12.5 V	f = 1 MHz		1.4		pF

2.2 Dynamic

Table 5. Dynamic

Symbol	Test conditions		Тур	Max	Unit
P3dB	$V_{DD} = 13.6 \text{ V}, I_{DQ} = 350 \text{ mA}$ f = 945 MHz	35			W
G _P	$V_{DD} = 13.6 \text{ V}, I_{DQ} = 350 \text{ mA}, P_{OUT} = 15 \text{ W}, f = 945 \text{ MHz}$	15	17.5	_	dB
h_{D}	$V_{DD} = 13.6 \text{ V}, I_{DQ} = 350 \text{ mA}, P_{OUT} = P3dB, f = 945 \text{ MHz}$	60	77		%
Load mismatch	V_{DD} = 17 V, I_{DQ} = 350 mA, P_{OUT} = 50 W, f = 945 MHz All phase angles	20:1			VSWR

2.3 ESD protection characteristics

Table 6. ESD protection characteristics

Test conditions	Class
Human body model	2
Machine model	M3

PD85035C Impedance

3 Impedance

Figure 2. Current conventions

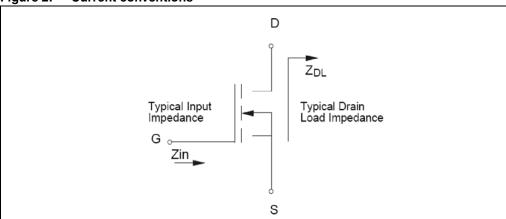


Table 7. Impedance data

Frequency (MHz)	Z _{IN} (Ω)	Z _{DL} (Ω)
945 MHz	1.08 +j 2.05	2.14 + j 2.17

4 Typical performances

Figure 3. Capacitances vs drain voltage

Figure 4. ID vs VGS

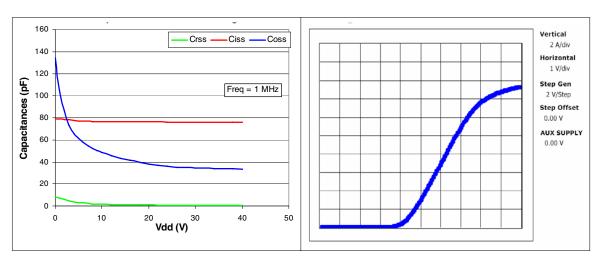
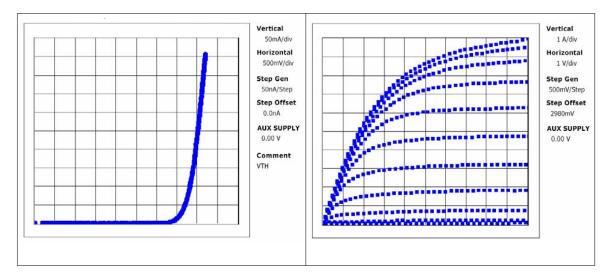


Figure 5. Threshold voltage

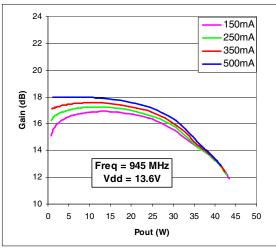
Figure 6. DC output characteristic



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Figure 7. Gain vs output power and bias current

Figure 8. Pout and efficiency vs input power



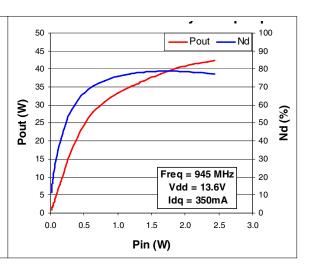
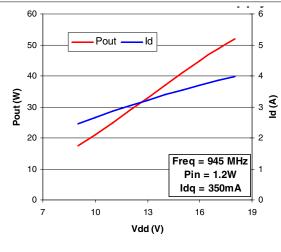
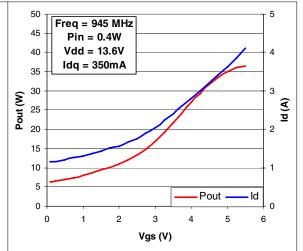


Figure 9. Pout and drain current vs supply voltage

Figure 10. Pout and drain current vs gate voltage





5 Package mechanical data

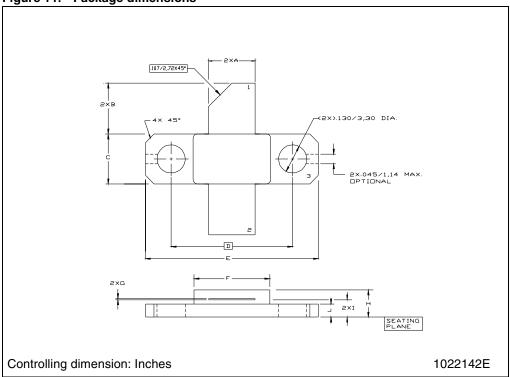
In order to meet environmental requirements, ST offers these devices in different grades of $\mathsf{ECOPACK}^{\mathbb{B}}$ packages, depending on their level of environmental compliance. $\mathsf{ECOPACK}^{\mathbb{B}}$ specifications, grade definitions and product status are available at: $\mathit{www.st.com}$. $\mathsf{ECOPACK}^{\mathbb{B}}$ is an ST trademark.

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Table 8. M243 (.230 x .360 2L N/HERM W/FLG) mechanical data

Dim.	mm		mm Inch		Inch	
	Min	Тур	Max	Min	Тур	Max
Α	5.21		5.72	0.205		0.225
В	5.46		6.48	0.215		0.255
С	5.59		6.10	0.220		0.240
D		14.27			0.562	
Е	20.07		20.57	0.790		0.810
F	8.89		9.40	0.350		0.370
G	0.10		0.15	0.004		0.006
Н	3.18		4.45	0.125		0.175
I	1.83		2.24	0.072		0.088
J	1.27		1.78	0.050		0.070

Figure 11. Package dimensions



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Revision history PD85035C

6 Revision history

Table 9. Document revision history

Date	Revision	Changes	
16-Nov-2007	1	Initial release	
02-Jul-2009	2	Document status promoted from preliminary data to datasheet	

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